

## **isc** Silicon NPN Power Transistor

2SC3896

### **DESCRIPTION**

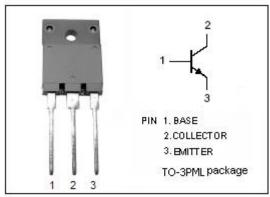
- · High Breakdown Voltage
- · High Switching Speed
- Wide Area of Safe Operation
- 100% avalanche tested
- Minimum Lot-to-Lot variations for robust device performance and reliable operation

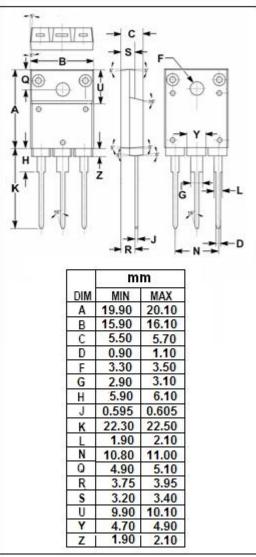
### **APPLICATIONS**

 Ultrahigh definition CRT display horizontal deflection output applications

# ABSOLUTE MAXIMUM RATINGS(Ta=25℃)

| SYMBOL           | PARAMETER  | VALUE   | UNIT       |
|------------------|--|---------|------------|
| V <sub>CBO</sub> | Collector-Base Voltage                               | 1500    | V          |
| V <sub>CEO</sub> | Collector-Emitter Voltage                            | 800     | V          |
| V <sub>EBO</sub> | Emitter-Base Voltage                                 | 6       | V          |
| Ic               | Collector Current- Continuous                        | 8       | А          |
| I <sub>CM</sub>  | Collector Current- Peak                              | 25      | A          |
| Pc               | Collector Power Dissipation @ $T_c$ =25 $^{\circ}$ C | 70      | W          |
| TJ               | Junction Temperature                                 | 150     | $^{\circ}$ |
| T <sub>stg</sub> | Storage Temperature Range                            | -55~150 | °C         |







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#### **ELECTRICAL CHARACTERISTICS**

 $T_c=25$ °C unless otherwise specified

| SYMBOL                | PARAMETER                            | CONDITIONS  | MIN | TYP. | MAX | UNIT       |  |  |
|-----------------------|--------------------------------------|---|-----|------|-----|------------|--|--|
| V <sub>CE</sub> (sat) | Collector-Emitter Saturation Voltage | I <sub>C</sub> = 5A; I <sub>B</sub> = 1.2A                          |     |      | 5.0 | V          |  |  |
| V <sub>BE</sub> (sat) | Base-Emitter Saturation Voltage      | I <sub>C</sub> = 5A; I <sub>B</sub> = 1.2A                          |     |      | 1.5 | V          |  |  |
| Ісво                  | Collector Cutoff Current             | V <sub>CB</sub> = 800V; I <sub>E</sub> = 0                          |     |      | 100 | μА         |  |  |
| I <sub>EBO</sub>      | Emitter Cutoff Current               | V <sub>EB</sub> =4V; I <sub>C</sub> = 0                             |     |      | 100 | uA         |  |  |
| h <sub>FE-1</sub>     | DC Current Gain                      | I <sub>C</sub> = 1A; V <sub>CE</sub> = 5V                           | 8   |      |     |            |  |  |
| h <sub>FE-2</sub>     | DC Current Gain                      | I <sub>C</sub> = 6A; V <sub>CE</sub> = 5V                           | 4   |      | 8   |            |  |  |
| Switching times       |                                      |   |     |      |     |            |  |  |
| t <sub>stg</sub>      | Storage Time                         |   |     |      | 3   | μS         |  |  |
| t <sub>f</sub>        | Fall Time                            | I <sub>C</sub> = 6A ;I <sub>B1</sub> =1.2A; I <sub>B2</sub> = -2.4A |     |      | 0.2 | μ <b>S</b> |  |  |

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